

1 ABSTRACT OF THE DISCLOSURE

2 The invention encompasses a method of forming a silicon-doped
3 aluminum oxide. Aluminum oxide and silicon monoxide are co-
4 evaporated. Subsequently, at least some of the evaporated aluminum
5 oxide and silicon monoxide is deposited on a substrate to form the
6 silicon-doped aluminum oxide on the substrate. The invention also
7 encompasses methods of forming transistors and flash memory devices.

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